

# LEGM200BA120L2H1

## IGBT Power Module

### Features

- $V_{CE}=1200V$   $I_C=200A$
- Low  $V_{CE(sat)}$
- $V_{CEsat}$  with positive temperature coefficient
- Maximum junction temperature 150°C
- Isolation Type Package

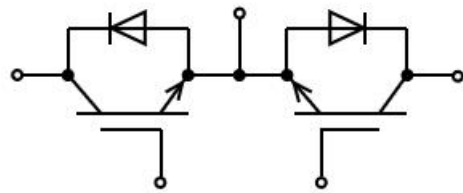
### Applications

- The inverter
- Motor control and drives

### Package Type & Internal Circuit



L2



Internal Circuit

### Maximum Rated Values (IGBT Inverter)

| Symbol    | Parameter                    | Conditions                              | Ratings  | Unit |
|-----------|------------------------------|---|----------|------|
| $V_{CES}$ | Maximum Power Dissipation    | $V_{EC}=0V, I_C=1mA, T_{vj}=25^\circ C$ | 1200     | V    |
| $I_C$     | Continuous Collector Current | $T_C=100^\circ C$                       | 200      | A    |
| $I_{CRM}$ | Peak Collector Current       | $I_{CRM}=2I_C$                          | 400      | A    |
| $V_{GES}$ | Gate-Emitter Voltage         | $T_{vj}=25^\circ C$                     | $\pm 30$ | V    |
| $P_{tot}$ | Total Power Dissipation      | $T_C=25^\circ C, T_{vjmax}=150^\circ C$ | 950      | W    |

**Maximum Rated Values (IGBT Inverter)**

| Symbol        | Parameter                              | Conditions   | Min. | Typ. | Max. | Unit             |    |
|---------------|--|--|------|------|------|------------------|----|
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage   | $I_C=200\text{ A}, V_{GE}=15\text{ V}, T_{vj}=25\text{ }^\circ\text{C}$  |      | 1.80 |      | V                |    |
|               |  | $I_C=200\text{ A}, V_{GE}=15\text{ V}, T_{vj}=125\text{ }^\circ\text{C}$   |      | 2.00 |      | V                |    |
| $V_{GE(th)}$  | Gate Threshold Voltage                 | $I_C=5.0\text{ mA}, V_{CE}=V_{GE}, T_{vj}=25\text{ }^\circ\text{C}$  |      | 5.8  |      | V                |    |
| $I_{CES}$     | Collector-Emitter Cut-off Current      | $V_{CE}=1200\text{ V}, V_{GE}=0\text{ V}, T_{vj}=25\text{ }^\circ\text{C}$   |      |      | 3.0  | mA               |    |
| $I_{GES}$     | Gate-Emitter Leakage Current           | $V_{CE}=0\text{ V}, V_{GE}=15\text{ V}, T_{vj}=25\text{ }^\circ\text{C}$   |      |      | 400  | nA               |    |
| $t_{d(on)}$   | Turn-on Delay Time, Inductive Load     | $I_C=200\text{ A}, V_{CE}=600\text{ V}$<br>$V_{GE}=\pm 15\text{ V}$<br>$R_{Gon}=2\ \Omega$<br>$T_{vj}=25\text{ }^\circ\text{C}$                        |      | 159  |      | ns               |    |
| $t_r$         | Rise Time, Inductive Load              |  |      | 64   |      | ns               |    |
| $t_{d(off)}$  | Turn-off Delay Time, Inductive Load    |  |      |      | 361  |                  | ns |
| $t_f$         | Fall Time, Inductive Load              |  |      |      | 107  |                  | ns |
| $E_{on}$      | Turn-on Energy Loss per Pulse          |  |      |      | 13.1 |                  | mJ |
| $E_{off}$     | Energy Loss per Pulse                  |  |      |      | 14.5 |                  | mJ |
| $t_{d(on)}$   | Turn-on Delay Time, Inductive Load     | $I_C=200\text{ A}, V_{CE}=600\text{ V}$<br>$V_{GE}=\pm 15\text{ V}$<br>$R_{Gon}=2\ \Omega$<br>$T_{vj}=125\text{ }^\circ\text{C}$                       |      | 170  |      | ns               |    |
| $t_r$         | Rise Time, Inductive Load              |  |      | 68   |      | ns               |    |
| $t_{d(off)}$  | Turn-off Delay Time, Inductive Load    |  |      |      | 431  |                  | ns |
| $t_f$         | Fall Time, Inductive Load              |  |      |      | 241  |                  | ns |
| $E_{on}$      | Turn-on Energy Loss per Pulse          |  |      |      | 14.1 |                  | mJ |
| $E_{off}$     | Energy Loss per Pulse                  |  |      |      | 22.7 |                  | mJ |
| $R_{thJC}$    | Thermal resistance, junction to case   | per IGBT   |      |      | 0.13 | K/W              |    |
| $T_{vj\ op}$  | Temperature under switching conditions |  | -40  |      | 125  | $^\circ\text{C}$ |    |
| $I_{sc}$      | SC                                     | $V_{GE}\leq 15\text{ V}, V_{CE}=600\text{ V},$<br>$t_p\leq 10\mu\text{s}, T_{vj}=125\text{ }^\circ\text{C},$<br>$V_{CEmax}=V_{CES}-L_{sCE}\cdot di/dt$ |      | 1100 |      | A                |    |

**Maximum Rated Values (Diode Inverter)**

| Symbol    | Parameter                       | Conditions   | Min. | Typ. | Max. | Unit                 |
|-----------|---------------------------------|--|------|------|------|----------------------|
| $V_{RRM}$ | Repetitive Peak Reverse Voltage | $T_{vj}=25\text{ }^{\circ}\text{C}$                                    |      | 1200 |      | V                    |
| $I_F$     | Continuous DC Forward Current   | $T_C=100\text{ }^{\circ}\text{C}$                                      |      | 200  |      | A                    |
| $I_{FRM}$ | Repetitive Peak Forward Current | $t_p=1\text{ ms}$  |      | 400  |      | A                    |
| $I^2t$    | $I^2t$ Value                    | $V_R=0\text{ V}, t_p=10\text{ ms}, T_{vj}=125\text{ }^{\circ}\text{C}$ |      | 7500 |      | $\text{A}^2\text{s}$ |

**Characteristic Values (Diode Inverter)**

| Symbol             | Parameter                            | Conditions  | Min.                                | Typ.             | Max.                                 | Unit               |
|--------------------|--------------------------------------|---|-------------------------------------|------------------|--------------------------------------|--------------------|
| $V_F$              | Forward Voltage                      | $I_F=200\text{ A}, V_{CE}=0\text{ V}, T_{vj}=25\text{ }^{\circ}\text{C}$  |                                     | 1.85             |                                      | V                  |
|                    |                                      | $I_F=200\text{ A}, V_{CE}=0\text{ V}, T_{vj}=125\text{ }^{\circ}\text{C}$ |                                     | 2.00             |                                      | V                  |
| $t_{rr}$           | Reverse Recovery time                | $I_F=200\text{ A}, V_R=600\text{ V}$<br>$-di/dt=1350\text{ A/us}$         |                                     | 144              |                                      | ns                 |
| $Q_r$              | Recovered Charge                     |   |                                     | 18.4             |                                      | $\mu\text{C}$      |
| $E_{rec}$          | Reverse Recovery Energy              |   | $T_{vj}=25\text{ }^{\circ}\text{C}$ |                  | 9.8                                  |                    |
| $t_{rr}$           | Reverse Recovery time                | $I_F=200\text{ A}, V_R=600\text{ V}$<br>$-di/dt=1350\text{ A/us}$         |                                     | 271              |                                      | ns                 |
|                    |                                      |   | $Q_r$                               | Recovered Charge |                                      | 30.9               |
| $E_{rec}$          | Reverse Recovery Energy              |   |                                     |                  | $T_{vj}=125\text{ }^{\circ}\text{C}$ |                    |
| $R_{thJC}$         | Thermal resistance, junction to case | per Diode   |                                     |                  | 0.19                                 | K/W                |
| $T_{vj\text{ op}}$ | Operating Junction Temperature       |   | -40                                 |                  | 125                                  | $^{\circ}\text{C}$ |

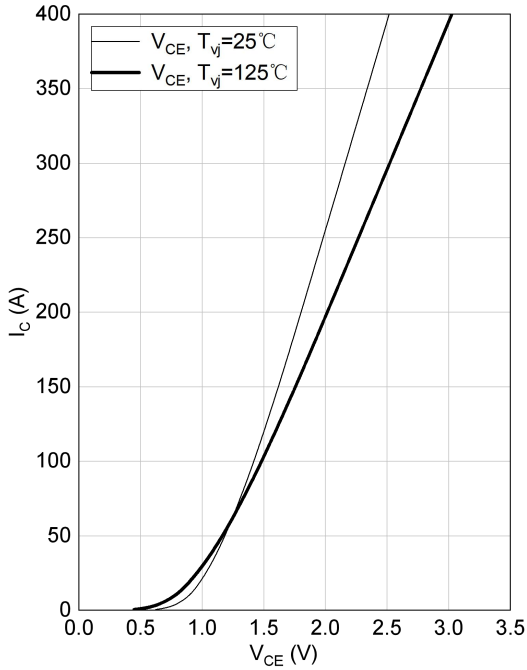
**Module Characteristics**

| Symbol     | Parameter                | Conditions                       | Min. | Typ. | Max. | Unit               |
|------------|--------------------------|----------------------------------|------|------|------|--------------------|
| $V_{isol}$ | Isolation voltage        | $t=1\text{ min}, f=50\text{ Hz}$ | 2500 |      |      | V                  |
| $T_{stg}$  | Storage Temperature      |                                  | -40  |      | 125  | $^{\circ}\text{C}$ |
| $M_t$      | Module Electrodes Torque | Recommended(M6)                  | 2.5  |      | 5.0  | N·m                |
| $M_s$      | Module-to-Sink Torque    | Recommended(M6)                  | 3.0  |      | 6.0  | N·m                |
| G          | Weight of Module         |                                  |      | 300  |      | g                  |

**Output characteristic of IGBT, Inverter (typical)**

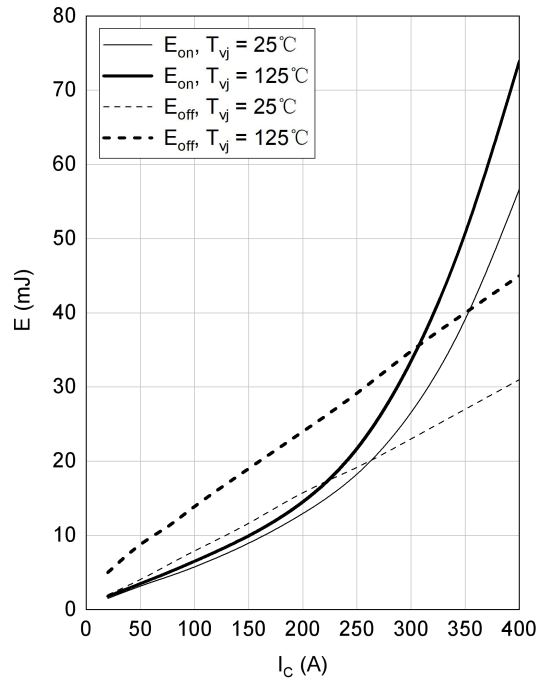
$$I_c = f(V_{CE})$$

$$V_{GE} = 15V$$


**Switching losses of IGBT, Inverter (typical)**

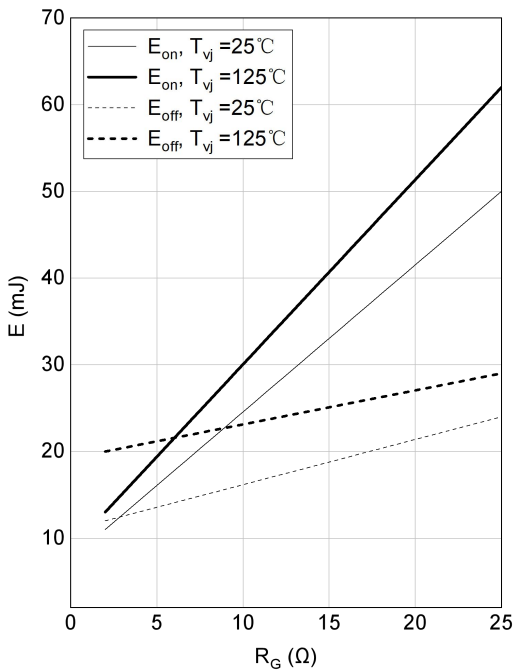
$$E_{on} = f(I_c), E_{off} = f(I_c)$$

$$V_{GE} = \pm 15V, R_G = 2\Omega, V_{CE} = 600V$$


**Switching losses of IGBT, Inverter (typical)**

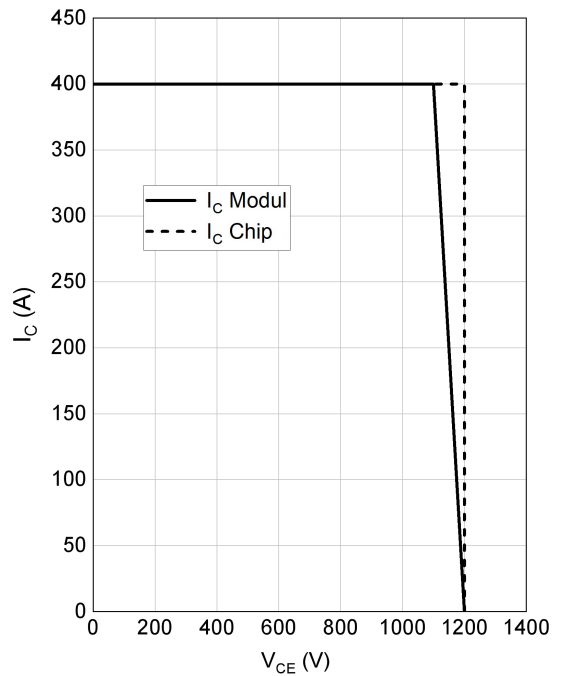
$$E_{on} = f(R_G), E_{off} = f(R_G)$$

$$V_{GE} = \pm 15V, I_c = 200A, V_{CE} = 600V$$


**RBSOA IGBT, Inverter (typical)**

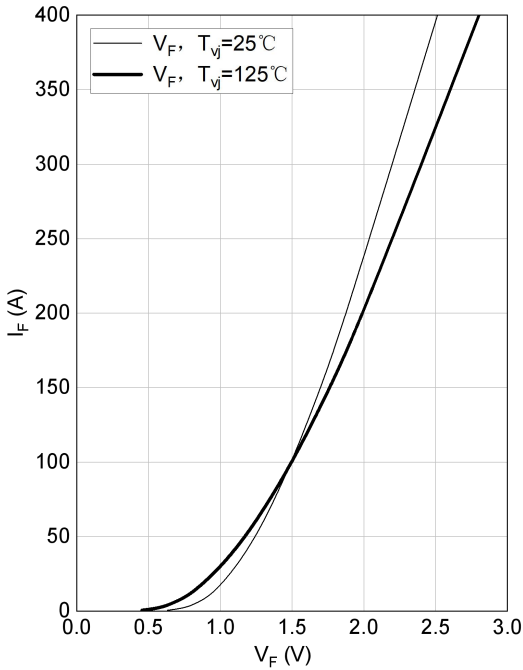
$$I_c = f(V_{CE})$$

$$V_{GE} = \pm 15V, R_{Goff} = 2\Omega, T_{vj} = 125^\circ C$$



Forward characteristic of Diode, Inverter (typical)

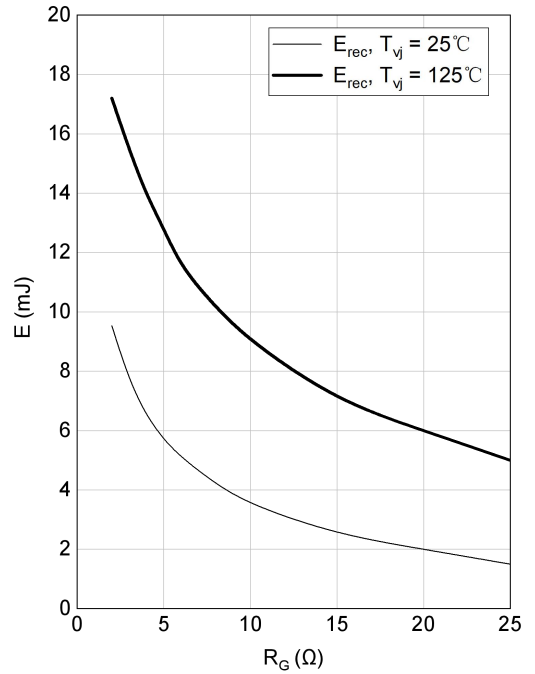
$$I_F = f(V_F)$$



Switching losses of Diode, Inverter (typical)

$$E_{rec} = f(R_G)$$

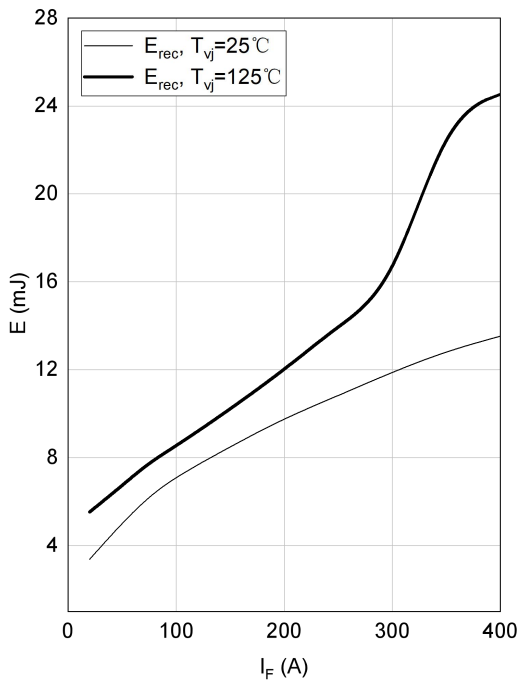
$$I_F = 200A, V_{CE} = 600V$$



Switching losses of Diode, Inverter (typical)

$$E_{rec} = f(I_F)$$

$$R_{Gon} = 2\Omega, V_{CE} = 600V$$





**DISCLAIMER**

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